YJG30N06AQ

N-Channel Enhancement Mode Field Effect Transistor

Product Summary

V_{DS}	60V
I_D	30A
$R_{DS(ON)}$(at V_{GS}=10V)	21m
$R_{DS(ON)}$(at V_{GS}=4.5V)	26m

100% EAS Tested 1 f)9o()-3r h[(e)99(n3((a)-5d)9[(j)-1(e)-s)7-[(j)-pa)-5a)

100%

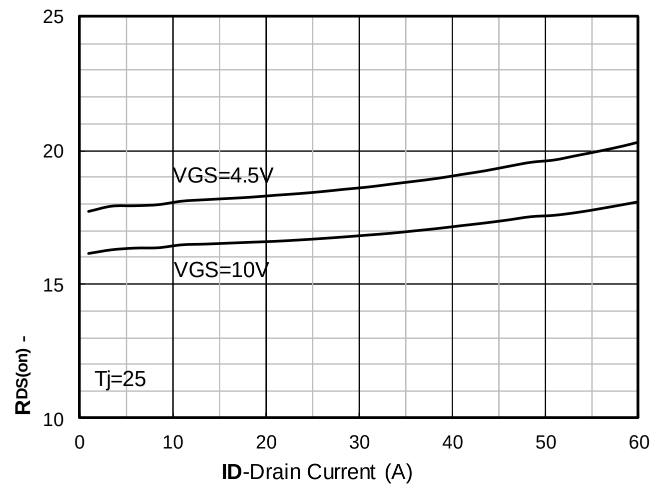

Figure 7. RDS(on) VS Drain Current

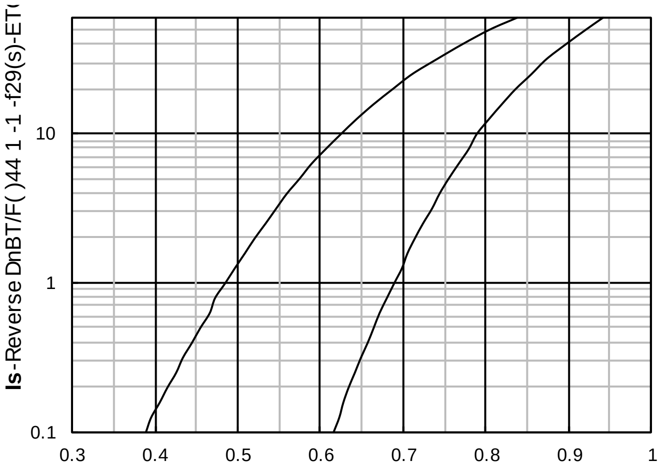

Figure 8. Forward characteristics of reverse diode

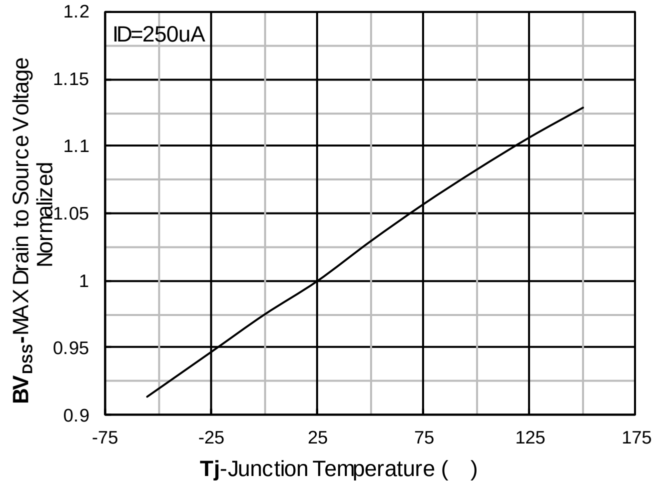

Figure 9. Normalized breakdown voltage

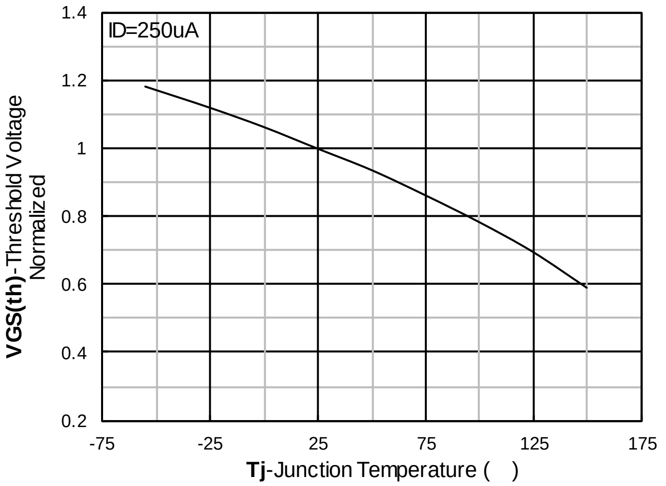

Figure 10. Normalized Threshold voltage

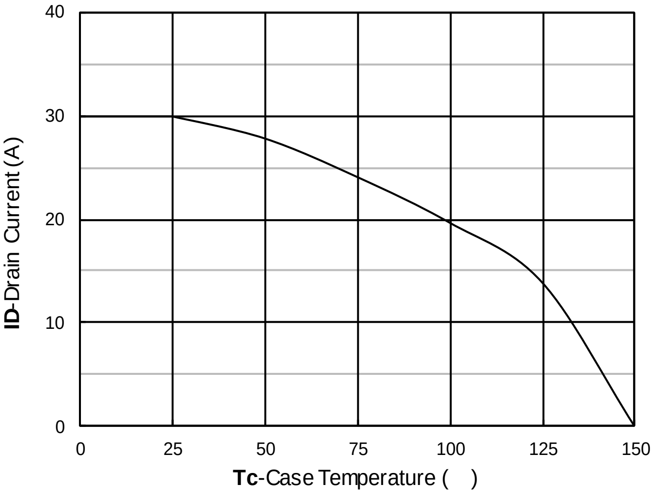

Figure 11. Current dissipation

Figure 12. Power dissipation

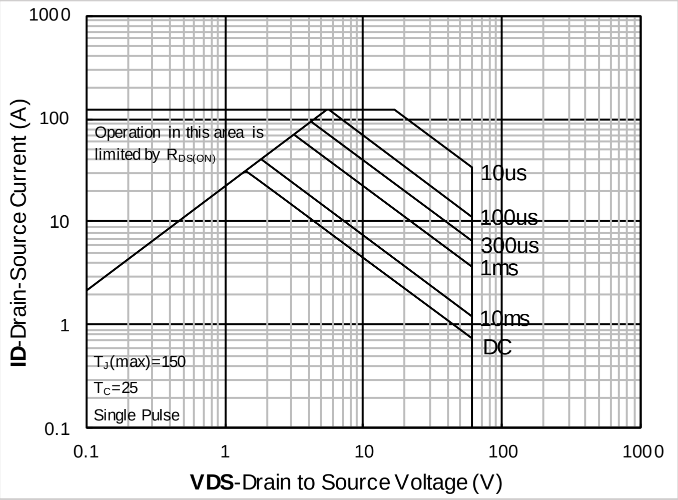

Figure 13. Maximum Transient Thermal Impedance

Figure 14. Safe Operation Area

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